

Suck-Whan Kim

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Insights into the growth of hexagonal Si crystals using Al-based nano absorber. Semiconductor Science and Technology, 2022, 37, 045016.	2.0	2
2	Optical property of hexagonal (2H) silicon crystal. Semiconductor Science and Technology, 2021, 36, 095023.	2.0	4
3	Growth of a Thick AlN Epilayer by Using the Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2020, 77, 282-287.	0.7	0
4	Comparison of AlN Nanowire-Like Structures Grown by using Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2019, 75, 242-247.	0.7	0
5	Growth of AlN Epilayers on Sapphire Substrates by Using the Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2019, 74, 1160-1165.	0.7	3
6	Vertical-type Blue Light Emitting Diode by Mixed-Source Hydride Vapor Phase Epitaxy Method. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700491.	1.8	3
7	Electrode-Evaporation Method of III-nitride Vertical-type Single Chip LEDs. Journal of the Korean Physical Society, 2018, 73, 1346-1350.	0.7	0
8	AlN and AlGaIn layers grown on Si(111) substrate by mixed-source hydride vapor phase epitaxy method. Japanese Journal of Applied Physics, 2017, 56, 01AD07.	1.5	5
9	Mechanism of light emission and manufacturing process of vertical-type light-emitting diode grown by hydride vapor phase epitaxy. Japanese Journal of Applied Physics, 2017, 56, 01AD03.	1.5	5
10	Growth of AlN layer on patterned sapphire substrate by hydride vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FC02.	1.5	10
11	Carbon microspheres grown by using hydride vapor phase epitaxy. Journal of the Korean Physical Society, 2015, 67, 1268-1272.	0.7	0
12	Thick AlN epilayer grown by using the HVPE method. Journal of the Korean Physical Society, 2015, 67, 643-647.	0.7	7